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DATASHEET

HS-390RH-T

Radiation HardenedCMOS Dual SPDT Analog Switch

Intersil's Satellite Applications FlowTM (SAF) devices are fully tested and guaranteed to 100kRAD total dose. This QML Class T device is processed to a standard flow intended to meet the cost and shorter lead-time needs of large volume satellite manufacturers, while maintaining a high level of reliability.

The HS-390RH-T analog switch is a monolithic device fabricated using Radiation Hardened CMOS technology and the Intersil dielectric isolation process for latch-up free operation. Improved total dose hardness is obtained by layout (thin oxide tabs extending to a channel stop) and processing (hardened gate oxide). These switches offer lowresistance switching performance for analog voltages up to the supply rails. "ON" resistance is low and stays reasonably constant over the full range of operating voltage and current. "ON" resistance also stays reasonably constant when exposed to radiation, being typically 30Ω pre-rad and 35Ω post 100kRAD(Si). Break-before-make switching is controlled by 5V digital inputs.

Specifications

Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). The SMD numbers listed below must be used when ordering.

Detailed Electrical Specifications for the HS-390RH-T are contained in SMD 5962-95813. A "hot-link" is provided from our website for downloading.

www.intersil.com/spacedefense/newsafclasst.asp

Intersil's Quality Management Plan (QM Plan), listing all Class T screening operations, is also available on our website.

www.intersil.com/quality/manuals.asp

Ordering Information

| ORDERING NUMBER | PART NUMBER | TEMP. RANGE (^o C) |
|--------------------|----------------|-------------------------------------|
| 5962R9581303TEC | HS1-390RH-T | -55 to 125 |
| 5962R9581303TYC | HS9-390RH-T | -55 to 125 |

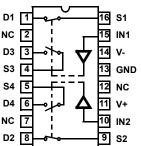
NOTE: Minimum order quantity for -T is 150 units through distribution, or 450 units direct.

Features

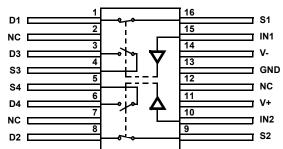
- QML Class T, Per MIL-PRF-38535
- Radiation Performance
 - Gamma Dose (γ) 1 x 10⁵ RAD(Si)
 - No Latch-Up, Dielectrically Isolated Device Islands
- Pin for Pin Compatible with Intersil HI-390 Series Analog Switches
- Analog Signal Range 15V
- Low Leakage 100nA (Max, Post Rad)
- Low r_{ON} 60Ω (Max, Post Rad)
- Low Operating Power. 100µA (Max, Post Rad)

Pinouts

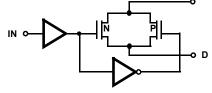








Functional Diagram



TRUTH TABLE

| LOGIC | SW1 SW2 | SW3 SW4 |
|-------|---------|---------|
| 0 | OFF | ON |
| 1 | ON | OFF |

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FN4604 Rev 1.00 July 1999

Die Characteristics

DIE DIMENSIONS:

(2130μm x 1930μm x 279μm ±25.4μm) 84 x 76 x 11mils ±1mil

METALLIZATION:

Type: Al Thickness: 12.5kÅ ±2kÅ

SUBSTRATE POTENTIAL:

Unbiased (DI)

BACKSIDE FINISH:

Gold

Metallization Mask Layout

PASSIVATION:

Type: Silox (S_iO₂) Thickness: 8.0kÅ ±1.0kÅ

WORST CASE CURRENT DENSITY:

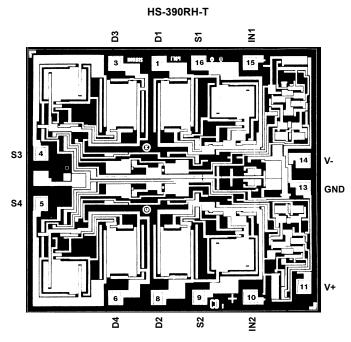
< 2.0e5 A/cm²

TRANSISTOR COUNT:

76

PROCESS:

Metal Gate CMOS, Dielectric Isolation



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